

N- and P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.060 at $V_{GS} = 4.5$ V	3.4
		0.070 at $V_{GS} = 2.5$ V	3.2
		0.100 at $V_{GS} = 1.8$ V	2.5
P-Channel	- 20	0.110 at $V_{GS} = - 4.5$ V	- 2.5
		0.145 at $V_{GS} = - 2.5$ V	- 2.0
		0.220 at $V_{GS} = - 1.8$ V	- 1.0

FEATURES

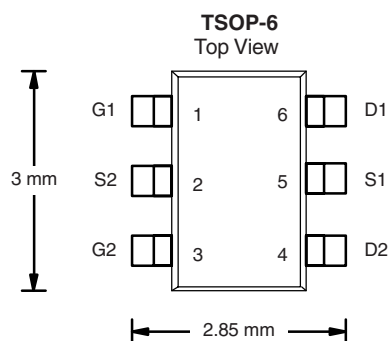
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Fast Switching In Small Footprint
- Very Low $R_{DS(on)}$ for Increased Efficiency
- Compliant to RoHS Directive 2002/95/EC



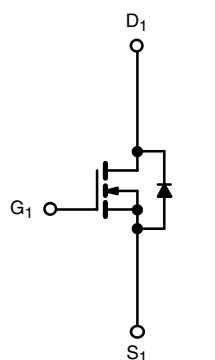
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

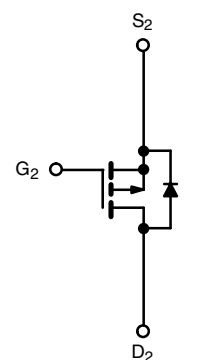
- Load Switch for Portable Devices



Ordering Information: Si3586DV-T1-E3 (Lead (Pb)-free)
Si3586DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V _{DS}	20		- 20		V
Gate-Source Voltage		V _{GS}	± 8				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	3.4	2.9	- 2.5	- 2.1	A
	T _A = 70 °C		2.7	2.3	- 2.0	- 1.7	
Pulsed Drain Current		I _{DM}	± 8				
Continuous Source Current (Diode Conduction) ^a		I _S	1.05	0.75	- 1.05	- 0.75	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	1.15	0.83	1.15	0.83	W
	T _A = 70 °C		0.73	0.53	0.73	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	93	110	$^\circ\text{C/W}$
	Steady State		130	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	90	90	

Note:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.40		1.1	V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.40		- 1.1	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	N-Ch			± 100	nA
		V _{DS} = 0 V, V _{GS} = ± 8 V	P-Ch			± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 85 °C	N-Ch			10	
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 85 °C	P-Ch			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	5			A
		V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	P-Ch	- 5			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.4 A	N-Ch		0.047	0.060	Ω
		V _{GS} = - 4.5 V, I _D = - 2.5 A	P-Ch		0.086	0.110	
		V _{GS} = 2.5 V, I _D = 3.2 A	N-Ch		0.054	0.070	
		V _{GS} = - 2.5 V, I _D = - 2.0 A	P-Ch		0.116	0.145	
		V _{GS} = - 1.8 V, I _D = - 2.5 A	N-Ch		0.075	0.100	
		V _{GS} = - 1.8 V, I _D = - 1.0 A	P-Ch		0.170	0.220	
Forward Transconductance ^a	g _{fs}	V _{DS} = 5 V, I _D = 3.4 A	N-Ch		13		S
		V _{DS} = - 5 V, I _D = - 2.5 A	P-Ch		6		
Diode Forward Voltage ^a	V _{SD}	I _S = 1.05 A, V _{GS} = 0 V	N-Ch		0.8	1.1	V
		I _S = - 1.05 A, V _{GS} = 0 V	P-Ch		- 0.8	- 1.1	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 3.4 A	N-Ch		4.1	6.0	nC
Gate-Source Charge	Q _{gs}		P-Ch		5	7.5	
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 2.5 A	N-Ch		0.65		
			P-Ch		0.68		
Gate Resistance	R _g		N-Ch		0.8		Ω
			P-Ch		1.3		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _G = 6 Ω	N-Ch		2.6	45	ns
Rise Time	t _r		P-Ch		9.8	45	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 10 V, R _L = 10 Ω I _D ≅ - 1 A, V _{GEN} = - 4.5 V, R _G = 6 Ω	N-Ch		30	85	
			P-Ch		52	85	
Fall Time	t _f		N-Ch		25	40	
			P-Ch		55	85	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.05 A, dI/dt = 100 A/μs	N-Ch		20	30	
		I _F = - 1.05 A, dI/dt = 100 A/μs	P-Ch		32	50	
					25	40	

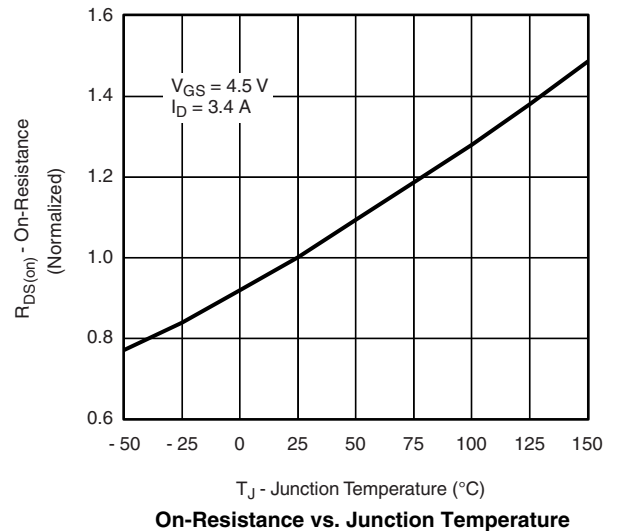
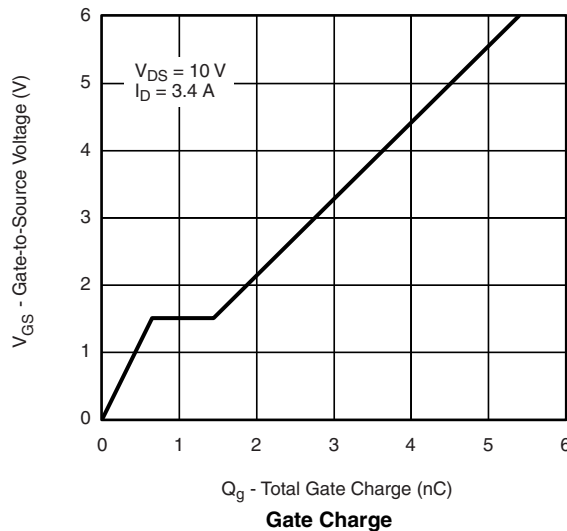
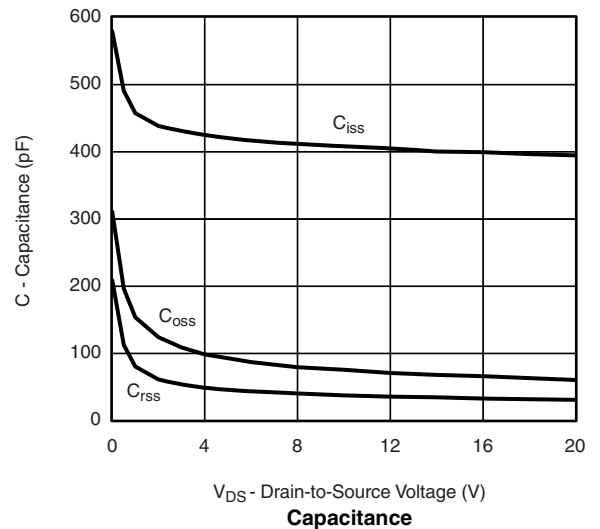
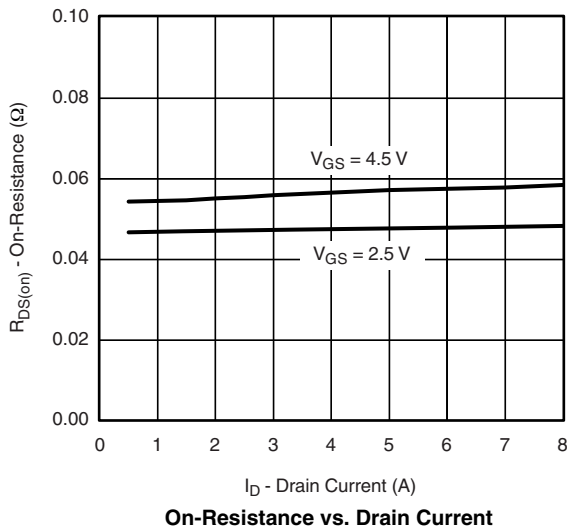
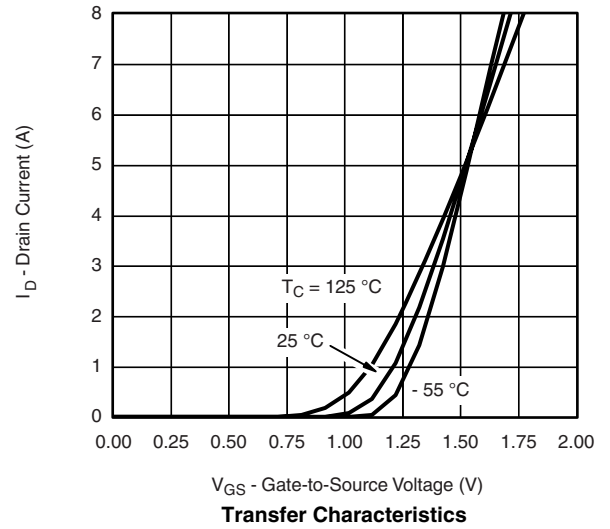
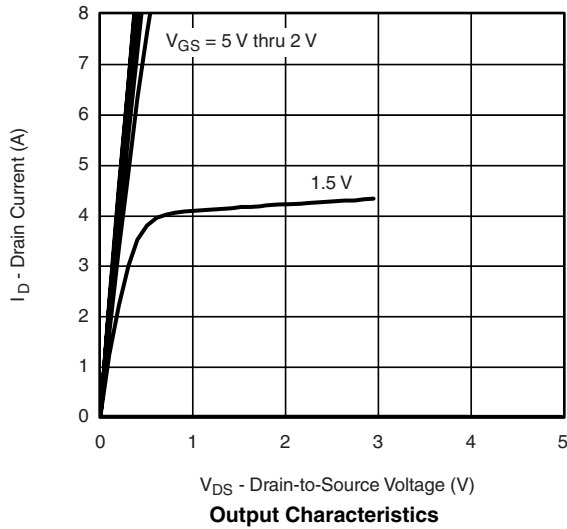
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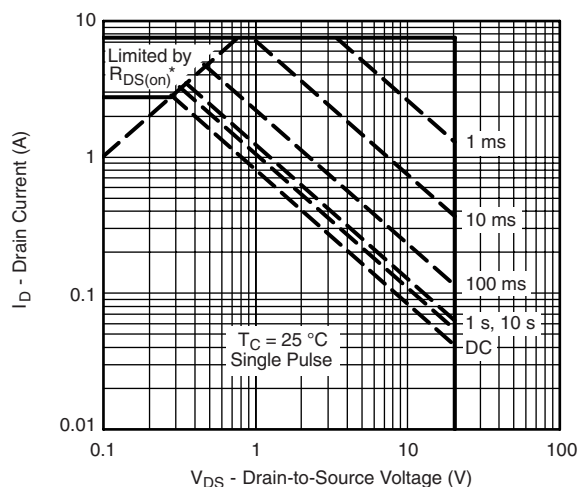
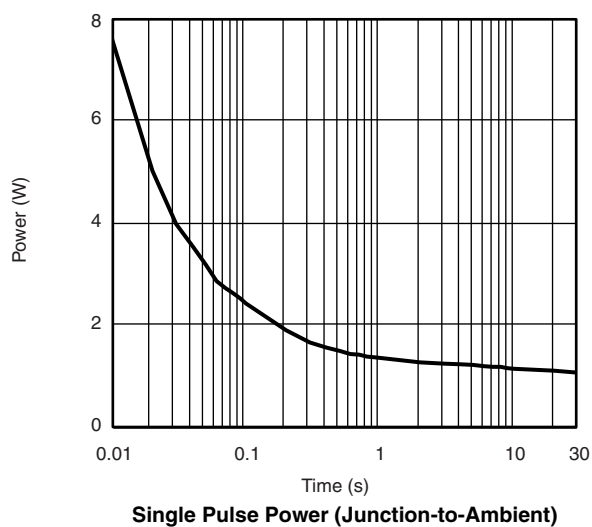
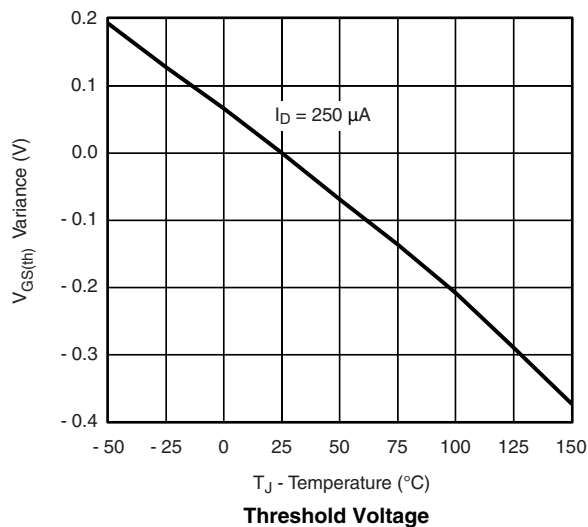
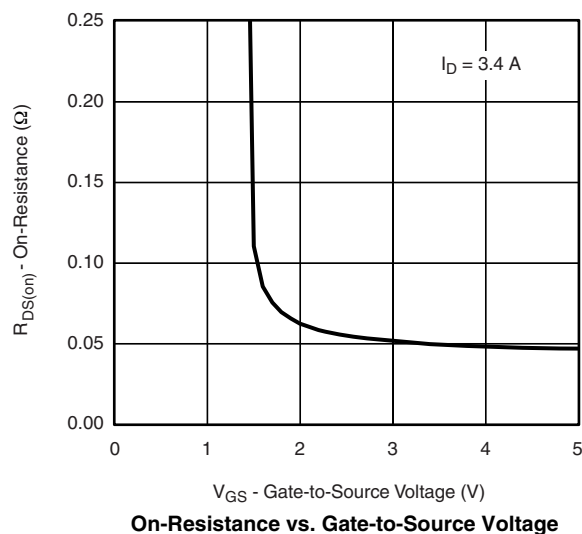
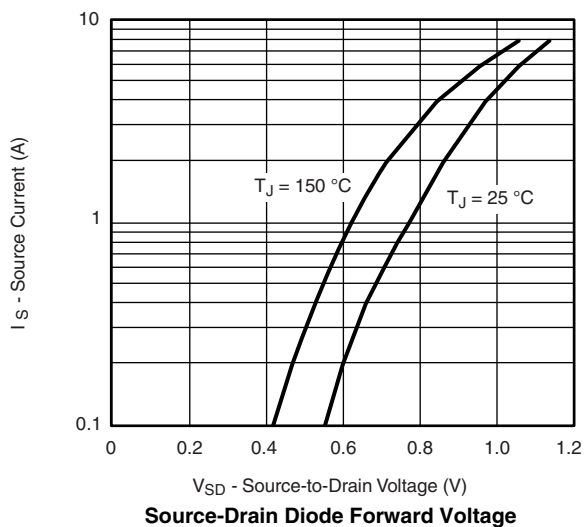
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

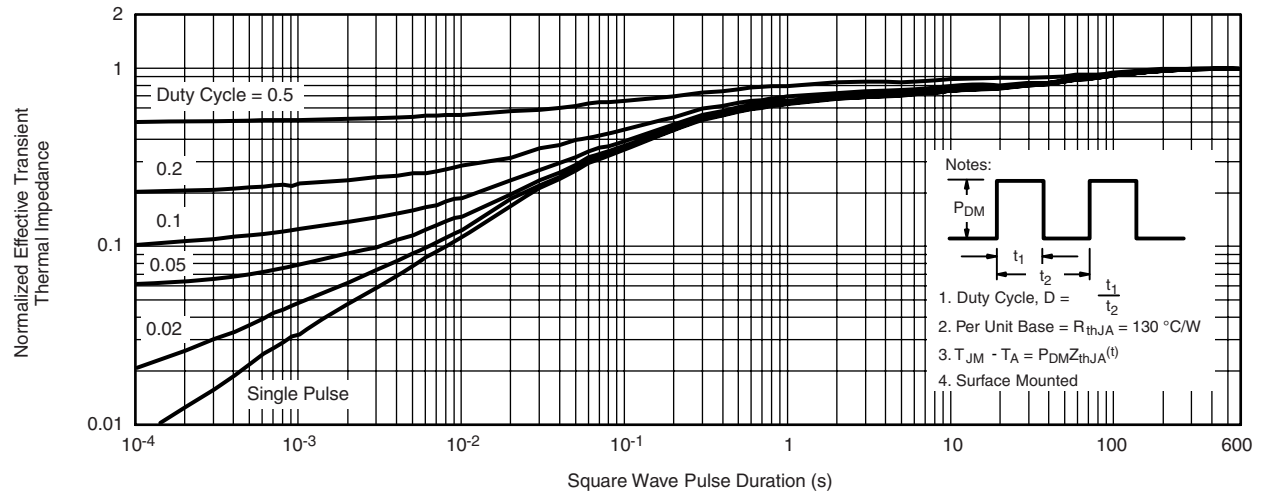


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

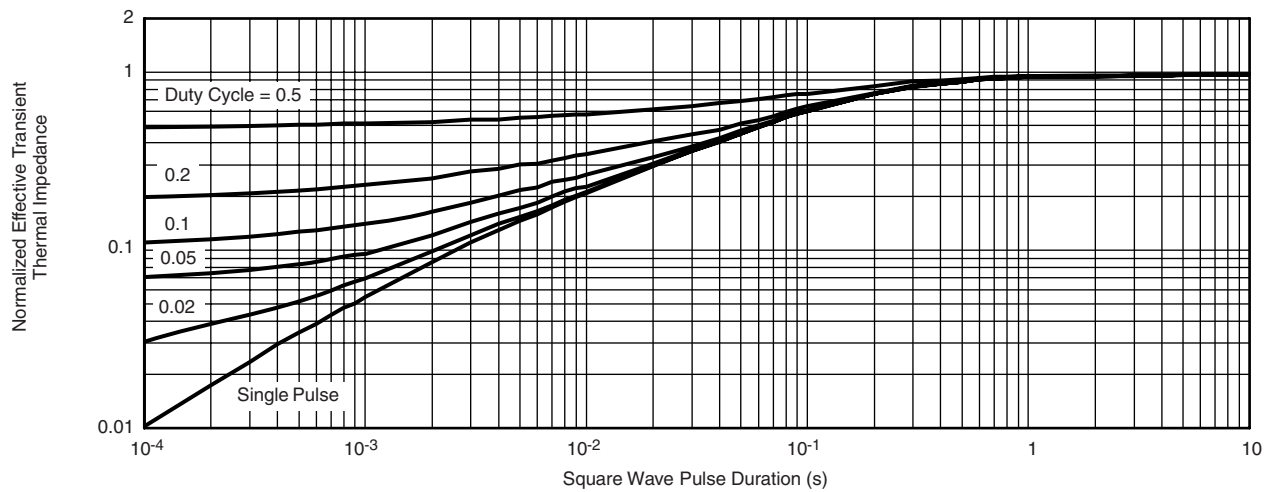
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

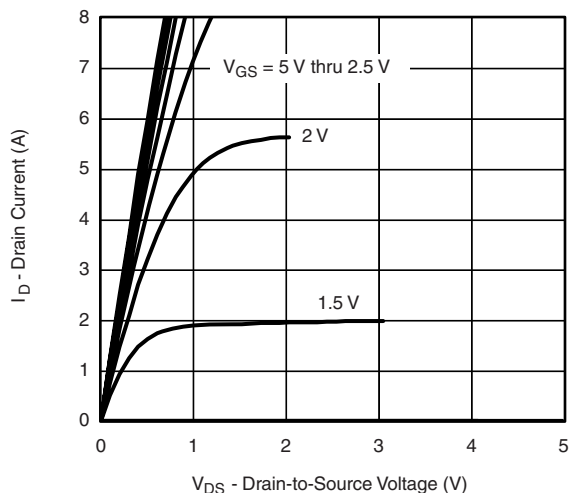
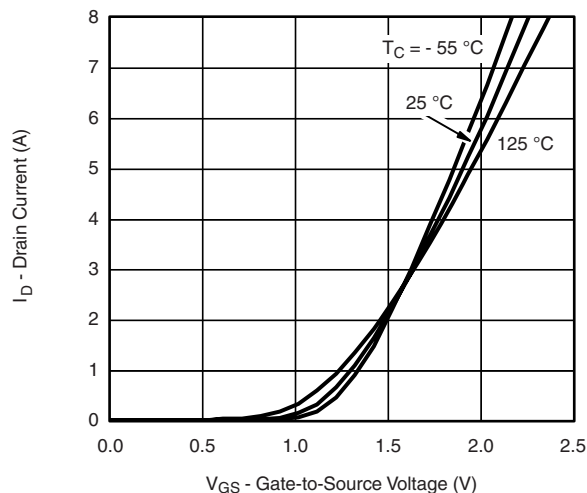
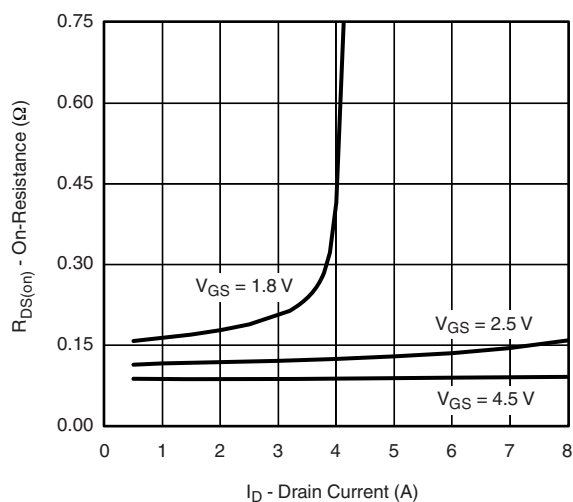
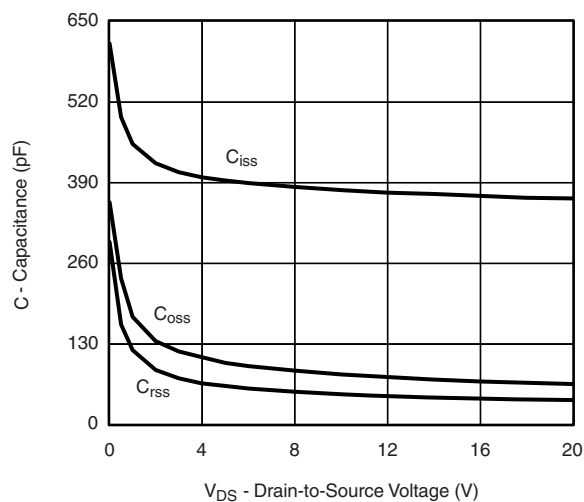
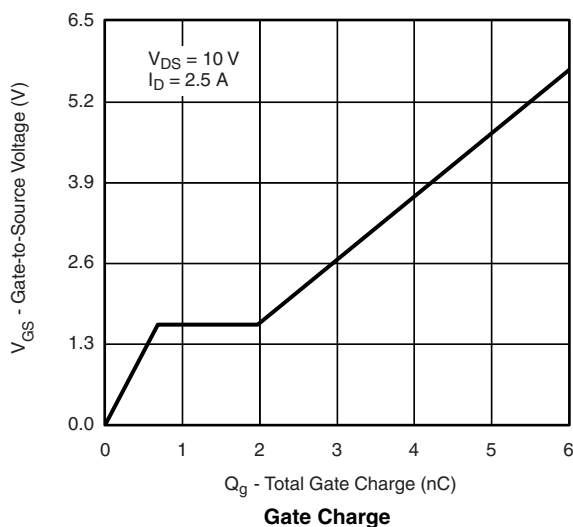
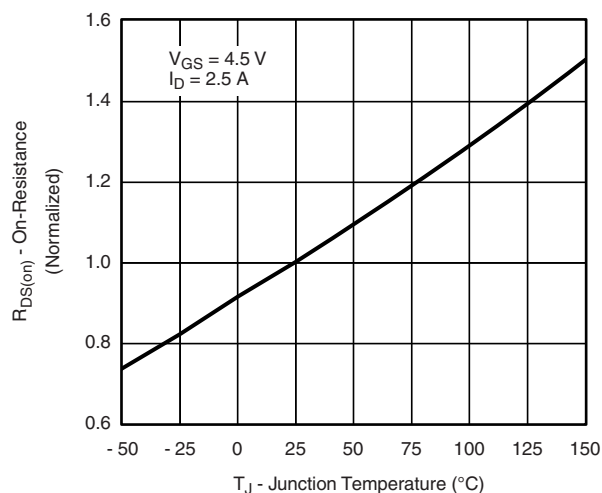
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



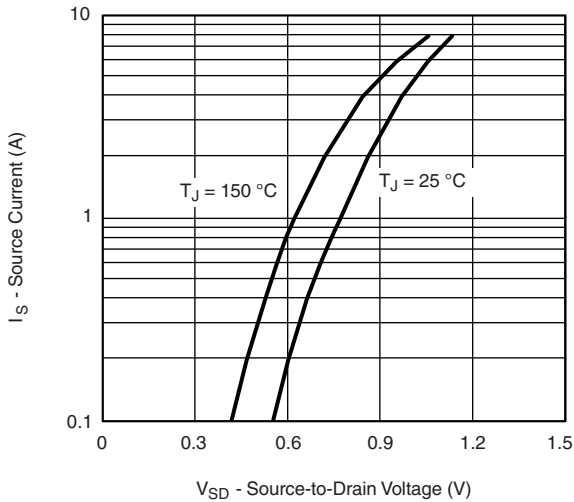
Normalized Thermal Transient Impedance, Junction-to-Ambient



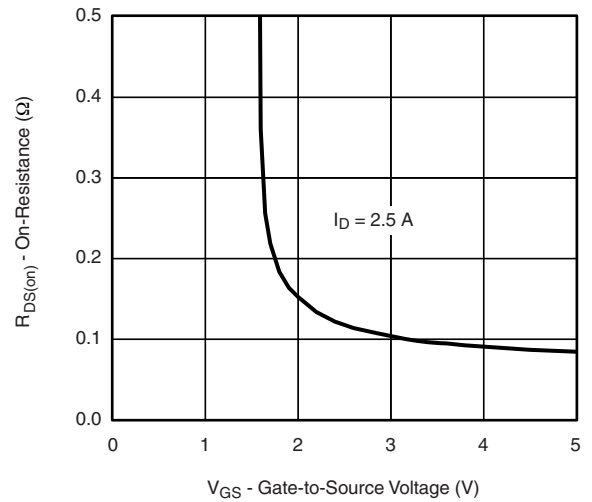
Normalized Thermal Transient Impedance, Junction-to-Foot

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

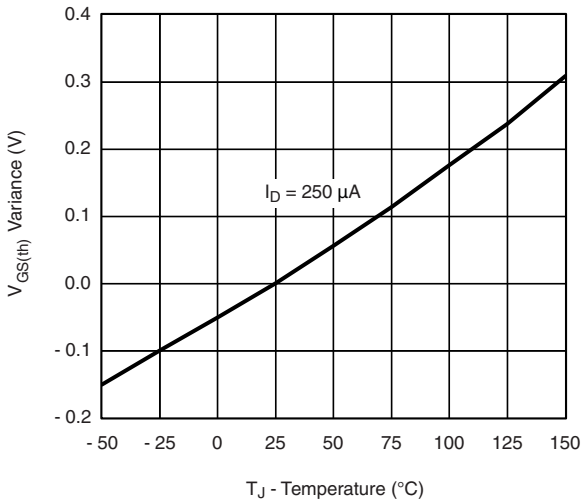
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



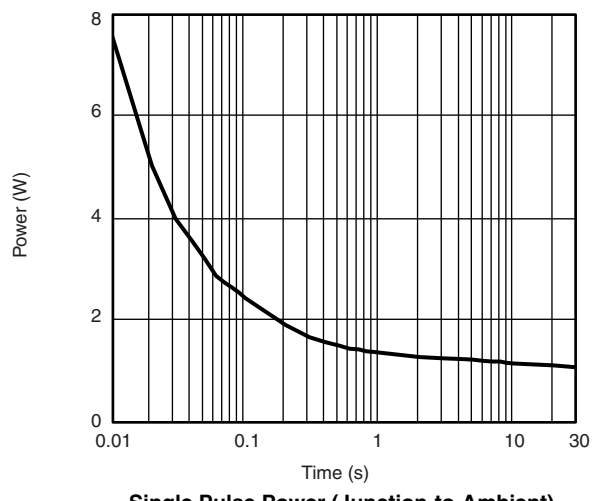
Source-Drain Diode Forward Voltage



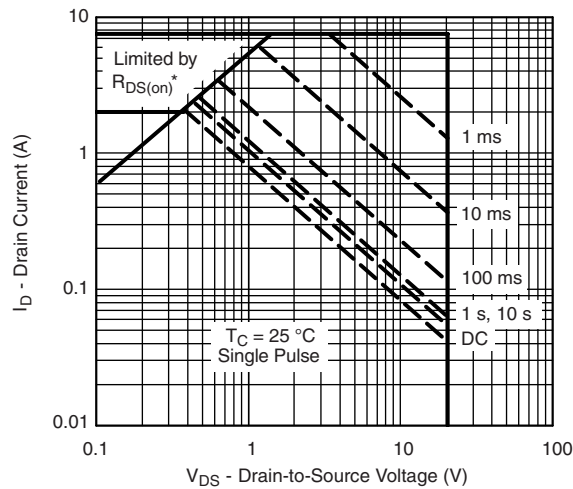
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

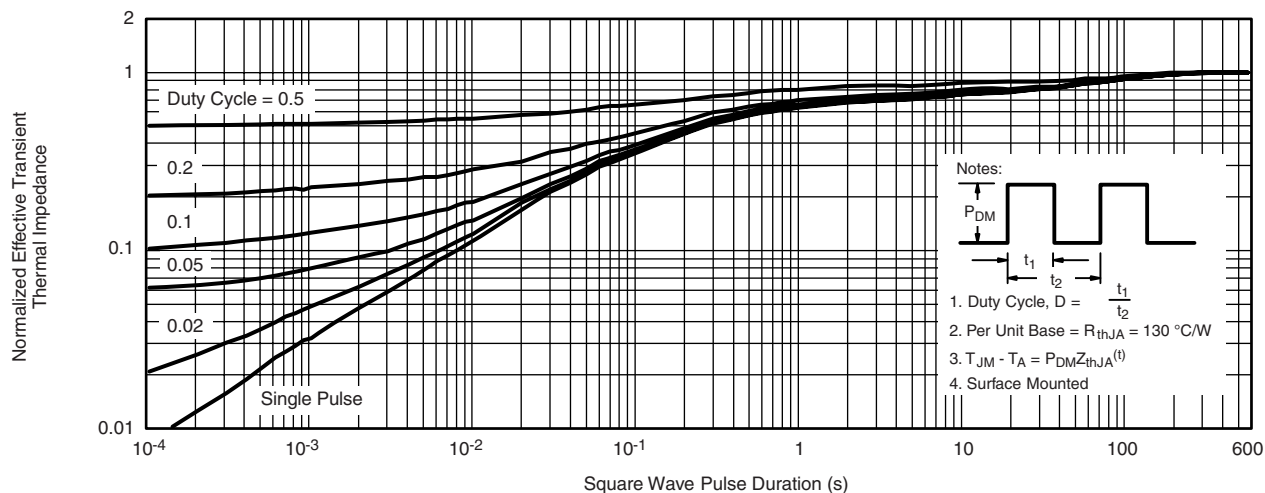
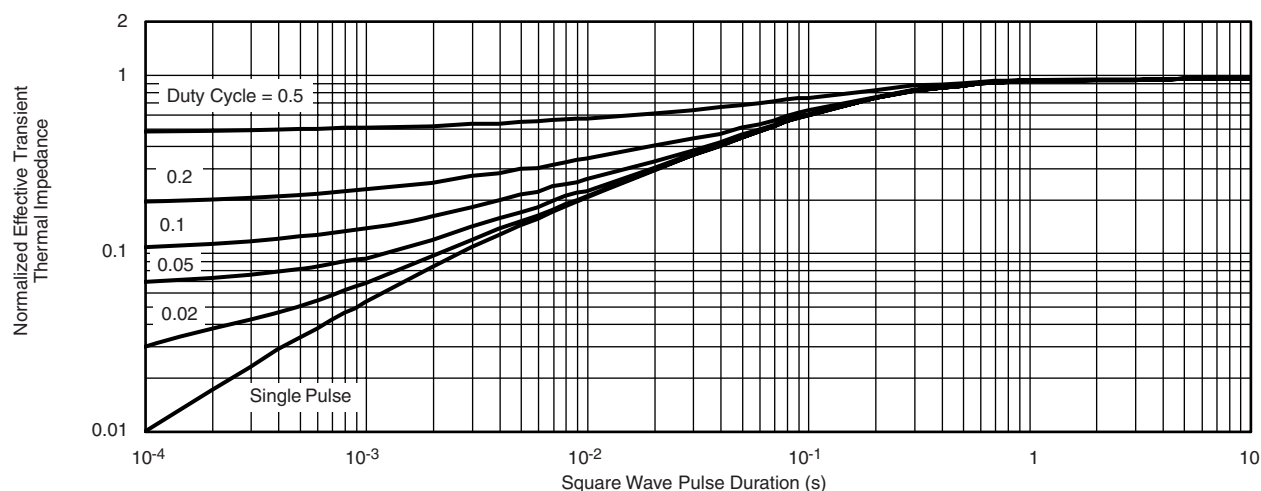


Single Pulse Power (Junction-to-Ambient)



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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